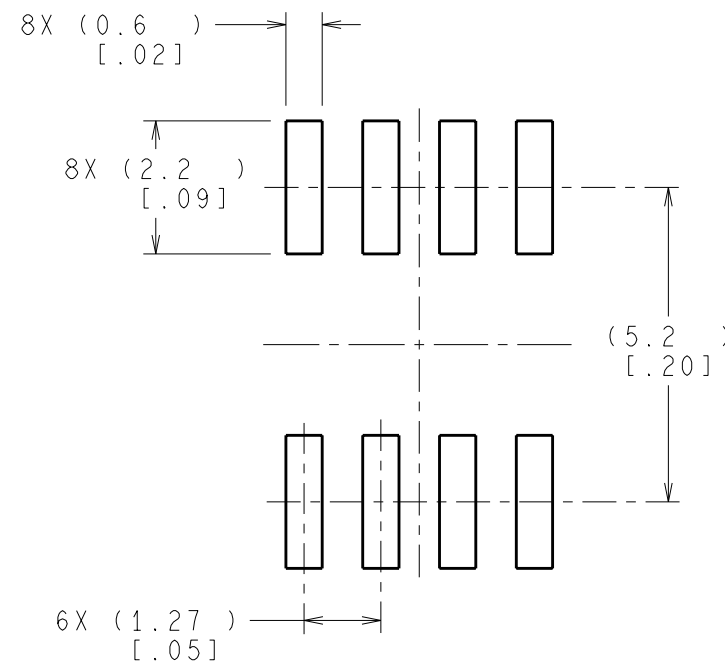
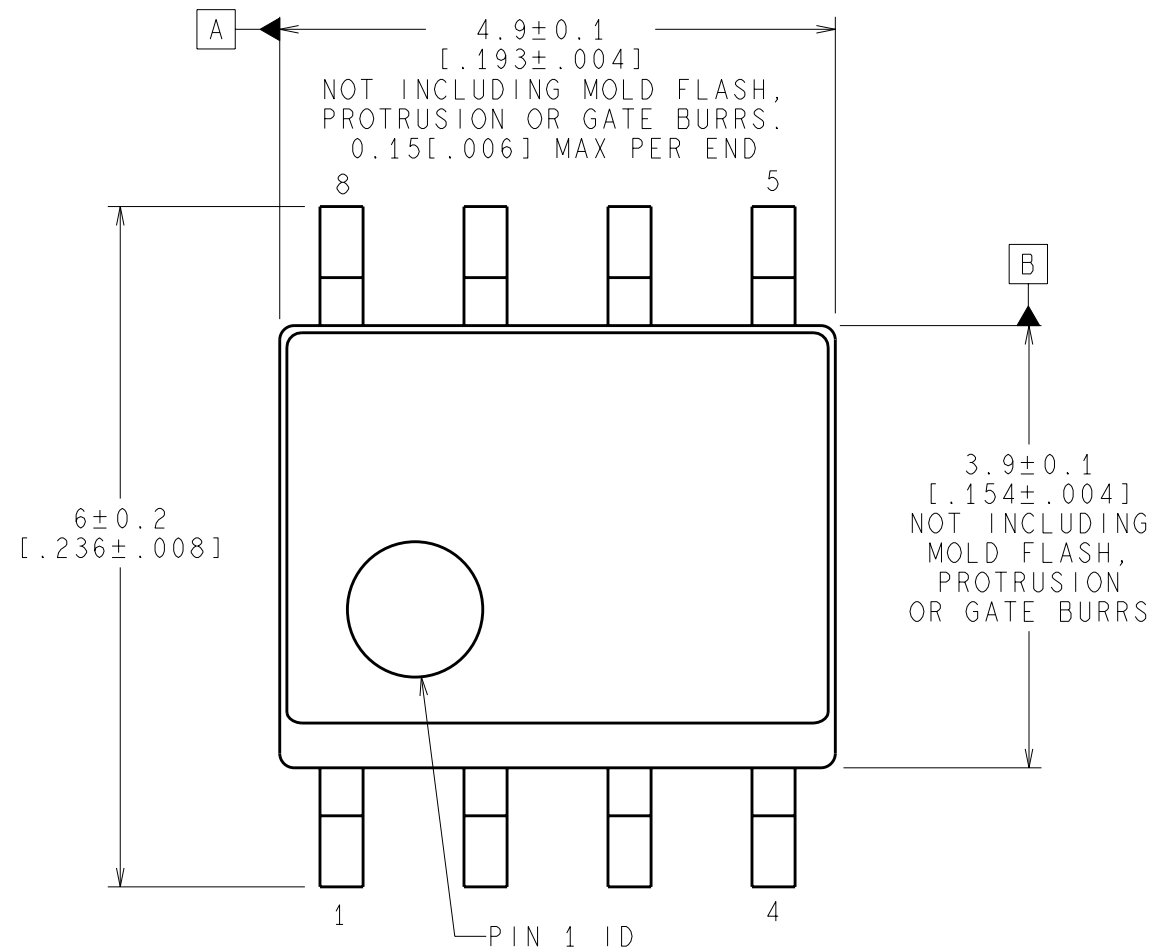
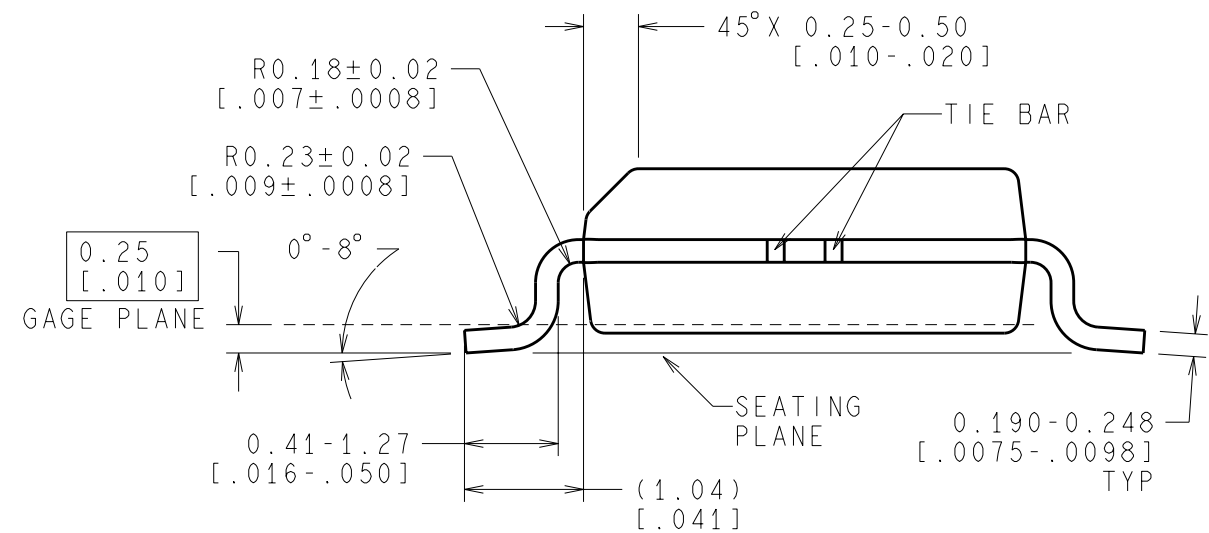
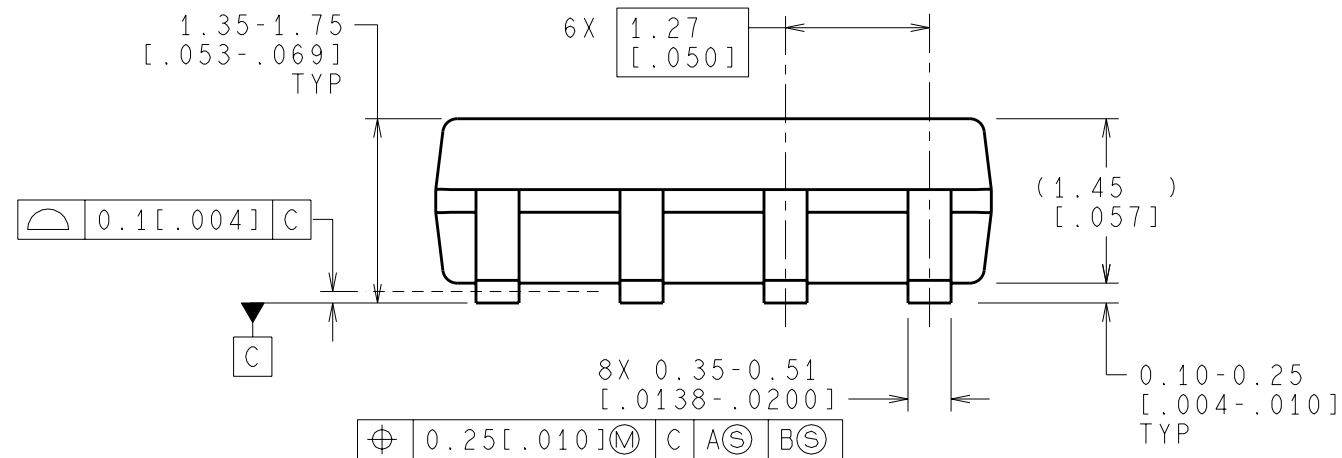


REVISIONS				
REV	DESCRIPTION	E.C.N.	DATE	BY/APP'D
J	CHGE LD SHAPE FROM TAPER TO SQUARE; REVISE PER CURRENT STD; REDRAW	11246	01/19/1996	MS/CS
K	DIM 1.35-1.75(.053-.069) WAS .069 [1.75] MAX; DIM 45° x 0.25-.050(.010-.020) WAS 45° x .017; REVISE DWG PER JEDEC STD; CONVERT CONTROLLING DIM TO MILLIMETER; DELETE DET A & TRANSFER ITS DIM'S TO SIDE VIEW; ADD RECOMMENDED LAND PATTERN DETAIL; REVISE NOTES; REVISE DWG TITLE; CHANGE DWG FORMAT TO B SIZE.	1727	02/14/2005	AS-MS/ TL/SN
L	REVISE DWG TITLE.	2187	09/15/2006	MS/MS
M	ADD TIE BAR AT SIDE OF PACKAGE; ADD "PROTRUSION OR GATE BURRS" TO DIM. 4.9 & DIM. 3.9	2820	05/29/2009	TKY/EL



RECOMMENDED LAND PATTERN



NOTES: UNLESS OTHERWISE SPECIFIED

- FOR LEAD FINISH THICKNESS AND COMPOSITION, SEE "SOLDER INFORMATION" IN THE PACKAGING SECTION OF THE NATIONAL SEMICONDUCTOR WEB PAGE (www.national.com).
- REFERENCE JEDEC REGISTRATION MS-012, VARIATION AA.

CONTROLLING DIMENSION IS MILLIMETER
VALUES IN [] ARE INCHES
DIMENSIONS IN () FOR REFERENCE ONLY

APPROVALS	DATE	National Semiconductor		
DRAWN MARTA SUCHY	01/19/1996	2900 Semiconductor Dr., Santa Clara, CA 95052-8090		
DFTG. CHK. T. LEQUANG & E. LEE	05/29/2009	SOIC NARROW, 4.9x3.9x1.45mm, 8 LD, 1.27mm PITCH		
ENGR. CHK. TK YII	05/29/2009			
PROJECTION	SCALE	SIZE	DRAWING NUMBER	REV
	NTS	B	(SC)MKT-M08A	M
FORMERLY: N/A	SHEET 1 of 1			